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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re International Application of

Takashi MORISHITA et al.

International Application No.: PCT/JP99/05231

International filing date: September 24, 1999

For: SEMICONDUCTOR SUBSTRATE AND PRODUCTION METHOD  
THEREOF, SEMICONDUCTOR DEVICE USING THE SAME AND  
PRODUCTION METHOD THEREOF

VERIFICATION OF TRANSLATION

Honorable Commissioner of Patent and Trademark  
Washington, D.C. 20231  
Sir:

Yuichi SATOH residing at c/o TANI & ABE, No. 6-20, Akasaka 2-chome,  
Minato-ku, Tokyo 107-0052, Japan, declares:

(1) that he knows well both the Japanese and English  
languages;

(2) that he translated the claims of the above-  
identified International Application from Japanese to English;

(3) that the attached English translation is a true  
and correct translation of the claims, specification and drawings  
of the above-identified International Application to the best  
of his knowledge and belief; and

(4) that all statements made of his own knowledge are  
true and that all statements made on information and belief are  
believed to be true, and further that these statements are made  
with the knowledge that willful false statements and the like  
are punishable by fine or imprisonment, or both, under 18 USC  
1001, and that such false statements may jeopardize the validity  
of the application or any patent issuing thereon.

March 1, 2001

Date

*Yuichi Satoh*

Yuichi SATOH